3.3 V LVTTL/LVCMOS to Differential LVPECL Translator

MC10EPT20, MC100EPT20

The MC10EPT20 is a 3.3 V TTL/CMOS to differential PECL translator. Because PECL (Positive ECL) levels are used, only +3.3 V and ground are required. The small outline SOIC–8 NB package and the single gate of the EPT20 makes it ideal for those applications where space, performance, and low power are at a premium.

The 100 Series contains temperature compensation.

Features

- 390 ps Typical Propagation Delay
- Maximum Input Clock Frequency > 1 GHz Typical
- Operating Range:
 - $V_{CC} = 3.0 \text{ V}$ to 3.6 V with GND = 0 V
- PNP TTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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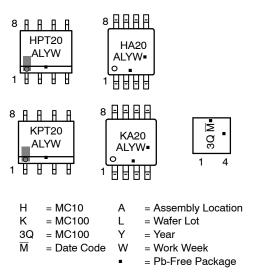
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SOIC-8 NB TSSOP-8 D SUFFIX DT SUFFIX M CASE 751-07 CASE 948R-02 C/

DFN-8 MN SUFFIX CASE 506AA

MARKING DIAGRAMS*

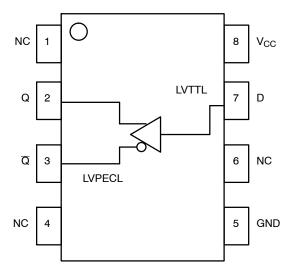


(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

^{*}For additional marking information, refer to Application Note <u>AND8002/D</u>.



PIN	FUNCTION					
Q, <u>Q</u>	Differential PECL Outputs					
D	LVTTL Input					
V _{CC}	Positive Supply					
GND	Ground					
NC	No Connect					
EP	(DFN8 only) Thermal exposed pad must be connected to a suffi- cient thermal conduit. Electrically connect to the most negative sup- ply (GND) or leave unconnected, floating open.					

Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 1.5 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
Transistor Count	150 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Power Supply	GND = 0 V		6	V
VI	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	6	V
I _{out}	Output Current	Continuous Surge		50 100	mA
TA	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θJC	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W
T _{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

Table 4. LVTTL INPUT DC CHARACTERISTICS (V_{CC} = 3.3 V, GND = 0 V, T_A = -40° C to $+85^{\circ}$ C)

Symbol	Characteristic	Min	Тур	Max	Unit
I _{IH}	Input HIGH Current (V _{in} = 2.7 V)			20	μA
I _{IHH}	Input HIGH Current MAX (V _{in} = 6.0 V)			100	μA
IIL	Input LOW Current (V _{in} = 0.5 V)			-0.6	mA
V _{IK}	Input Clamp Voltage (I _{in} = -18 mA)			-1.2	V
V _{IH}	Input HIGH Voltage	2.0			V
V _{IL}	Input LOW Voltage			0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

Table 5. 10EPT PECL OUTPUT DC CHARACTERISTICS (V_{CC} = 3.3 V, GND = 0 V (Note 1))

		−40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Icc	Positive Power Supply Current	18	23	28	18	23	28	19	24	29	mA
V _{OH}	Output HIGH Voltage (Note 2)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V _{OL}	Output LOW Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} – 2.0 V.

Table 6. 100EPT PECL OUTPUT DC CHARACTERISTICS (V_{CC} = 3.3 V, GND = 0 V (Note 1))

		–40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{CC}	Positive Power Supply Current	20	25	30	22	27	32	23	28	33	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} – 2.0 V.

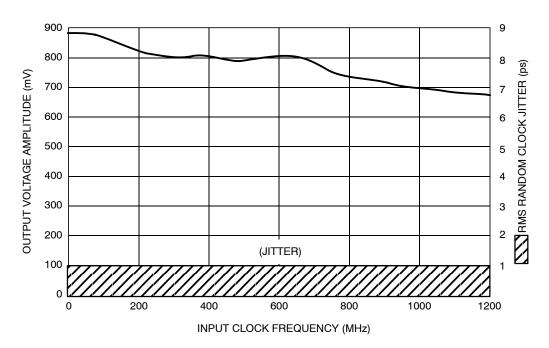
Table 7. AC CHARACTERISTICS (V_{CC} = 3.0 V to 3.6 V, GND = 0 V (Note 1))

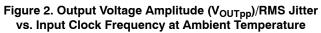
		−40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Input Clock Frequency		> 1			> 1			> 1		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential	280	350	430	300	370	450	320	400	490	ps
t _{SKEW}	Device-to-Device Skew (Note 2)			150			150			170	ps
t _{JITTER}	RMS Random Clock Jitter		1	2		1	2		1	2	ps
t _r t _f	Output Rise/Fall Times Q, Q (20% - 80%)	70	100	170	80	120	180	90	140	190	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Measured using a LVTTL source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

2. Skew is measured between outputs under identical transitions.





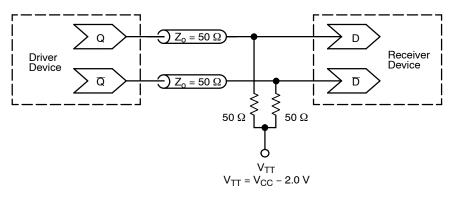


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10EPT20DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC10EPT20DTG	TSSOP–8 (Pb-Free)	100 Units/Tube
MC100EPT20DG	SOIC–8 NB (Pb-Free)	98 Units/Tube
MC100EPT20DR2G	SOIC–8 NB (Pb-Free)	2500 / Tape & Reel
MC100EPT20DTG	TSSOP–8 (Pb-Free)	100 Units/Tube
MC100EPT20DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100EPT20MNR4G	DFN-8 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

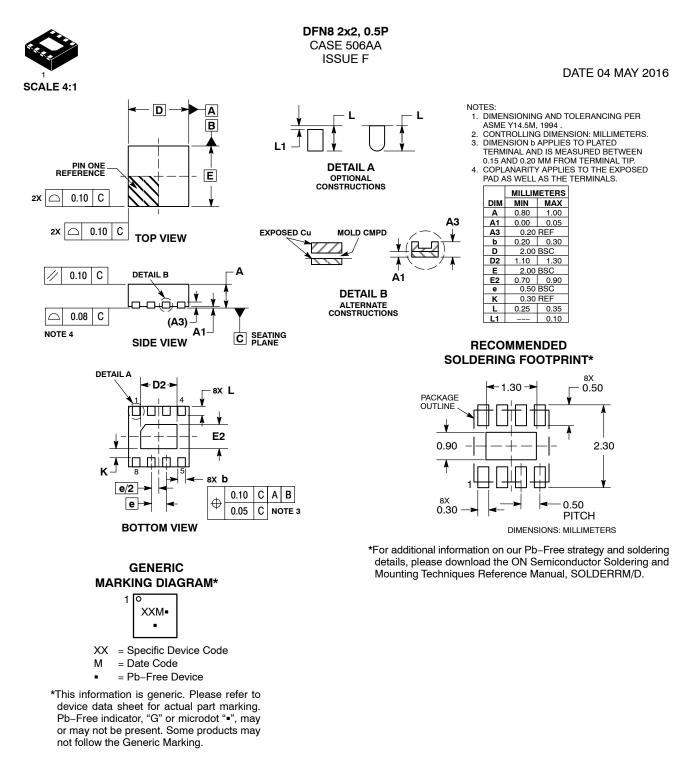
Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques
AN1406/D	-	Designing with PECL (ECL at +5.0 V)
AN1503/D	-	$ECLinPS^{^{\mathrm{TM}}} \text{ I/O SPiCE Modeling Kit}$
AN1504/D	-	Metastability and the ECLinPS Family
AN1568/D	-	Interfacing Between LVDS and ECL
AN1672/D	-	The ECL Translator Guide
AND8001/D	-	Odd Number Counters Design
AND8002/D	-	Marking and Date Codes
AND8020/D	-	Termination of ECL Logic Devices
AND8066/D	-	Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: CATHODE 1 PIN 1. 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC COMMON CATHODE/VCC 3 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

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STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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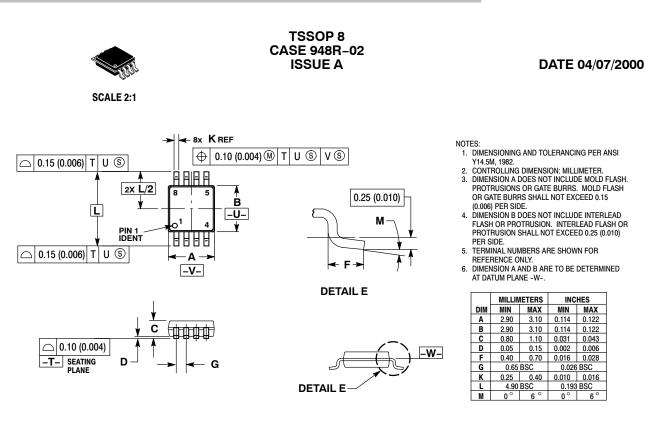
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